



ELC-455-34

Radiation	Type	Electrodes
blue	InGaN	P + N up

	<p>Description</p> <ul style="list-style-type: none"> - Substrate: sapphire, epitaxial layer: GaN based material - N bonding pad electrode: Au alloy - P bonding pad electrode: Au alloy <p><i>above drawing is not an real scale</i></p>
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Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I _F			20	mA
Forward voltage (DC)	100 mA	V _F			4	V
Junction temperature		T			100	°C
Peak forward current		I _{FM}			100	mA

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =20 mA	V _F		3.3	3.5	V
Reverse current	V _R =5 V	I _R			1	µA
Dominant wavelength	I _F =20 mA	λ _p		460		nm
Peak wavelength	I _F =20 mA	λ _p		455		nm
Full width at half maximum	I _F =20 mA	Δλ		30		nm
Output power	I _F =20 mA	Φ _e	22		24	mW

Packing

Chips on adhesive film with wire-bond side top



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.